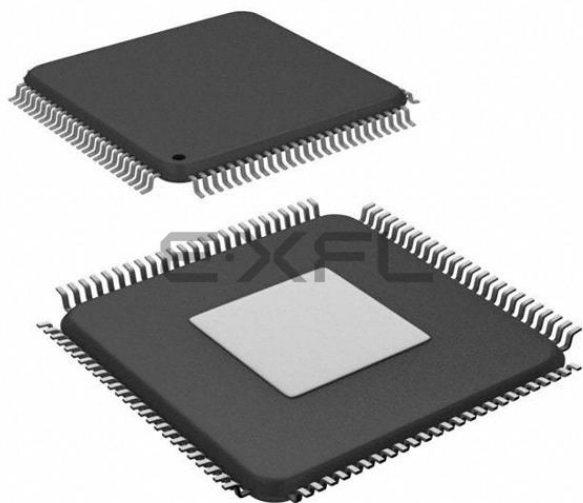




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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	EBI/EMI, I ² C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I ² S, POR, PWM, WDT
Number of I/O	75
Program Memory Size	320KB (320K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	34K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xe164hn40f80laafxuma1

Summary of Features

- On-Chip Peripheral Modules
 - Two synchronizable A/D Converters with up to 16 channels, 10-bit resolution, conversion time below 1 μ s, optional data preprocessing (data reduction, range check), broken wire detection
 - 16-channel general purpose capture/compare unit (CC2)
 - Two capture/compare units for flexible PWM signal generation (CCU6x)
 - Multi-functional general purpose timer unit with 5 timers
 - Up to 6 serial interface channels to be used as UART, LIN, high-speed synchronous channel (SPI/QSPI), IIC bus interface (10-bit addressing, 400 kbit/s), IIS interface
 - On-chip MultiCAN interface (Rev. 2.0B active) with 64 message objects (Full CAN/Basic CAN) on up to 2 CAN nodes and gateway functionality
 - On-chip system timer and on-chip real time clock
- Up to 12 Mbytes external address space for code and data
 - Programmable external bus characteristics for different address ranges
 - Multiplexed or demultiplexed external address/data buses
 - Selectable address bus width
 - 16-bit or 8-bit data bus width
 - Four programmable chip-select signals
- Single power supply from 3.0 V to 5.5 V
- Power reduction and wake-up modes
- Programmable watchdog timer and oscillator watchdog
- Up to 76 general purpose I/O lines
- On-chip bootstrap loaders
- Supported by a full range of development tools including C compilers, macro-assembler packages, emulators, evaluation boards, HLL debuggers, simulators, logic analyzer disassemblers, programming boards
- On-chip debug support via Device Access Port (DAP) or JTAG interface
- 100-pin Green LQFP package, 0.5 mm (19.7 mil) pitch

Ordering Information

The ordering code for an Infineon microcontroller provides an exact reference to a specific product. This ordering code identifies:

- the derivative itself, i.e. its function set, the temperature range, and the supply voltage
- the temperature range:
 - SAF-....: -40°C to 85°C
 - SAK-....: -40°C to 125°C
- the package and the type of delivery.

For ordering codes for the XE164xN please contact your sales representative or local distributor.

Key to Pin Definitions

- **Ctrl.:** The output signal for a port pin is selected by bit field PC in the associated register Px_IOCry. Output O0 is selected by setting the respective bit field PC to 1x00_B, output O1 is selected by 1x01_B, etc.
Output signal OH is controlled by hardware.
- **Type:** Indicates the pad type and its power supply domain (A, B, M, 1).
 - St: Standard pad
 - Sp: Special pad e.g. XTALx
 - DP: Double pad - can be used as standard or high speed pad
 - In: Input only pad
 - PS: Power supply pad

Table 5 Pin Definitions and Functions

Pin	Symbol	Ctrl.	Type	Function
3	$\overline{\text{TESTM}}$	I	In/B	Testmode Enable Enables factory test modes, must be held HIGH for normal operation (connect to V_{DDPB}). An internal pull-up device will hold this pin high when nothing is driving it.
4	P7.2	O0 / I	St/B	Bit 2 of Port 7, General Purpose Input/Output
	EMUX0	O1	St/B	External Analog MUX Control Output 0 (ADC1)
	TDI_C	IH	St/B	JTAG Test Data Input If JTAG pos. C is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it.
5	$\overline{\text{TRST}}$	I	In/B	Test-System Reset Input For normal system operation, pin $\overline{\text{TRST}}$ should be held low. A high level at this pin at the rising edge of $\overline{\text{PORST}}$ activates the XE164xN's debug system. In this case, pin $\overline{\text{TRST}}$ must be driven low once to reset the debug system. An internal pull-down device will hold this pin low when nothing is driving it.

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
19	P15.6	I	In/A	Bit 6 of Port 15, General Purpose Input
	ADC1_CH6	I	In/A	Analog Input Channel 6 for ADC1
20	V_{AREF}	-	PS/A	Reference Voltage for A/D Converters ADC0/1
21	V_{AGND}	-	PS/A	Reference Ground for A/D Converters ADC0/1
22	P5.0	I	In/A	Bit 0 of Port 5, General Purpose Input
	ADC0_CH0	I	In/A	Analog Input Channel 0 for ADC0
23	P5.2	I	In/A	Bit 2 of Port 5, General Purpose Input
	ADC0_CH2	I	In/A	Analog Input Channel 2 for ADC0
	TDI_A	I	In/A	JTAG Test Data Input
24	P5.3	I	In/A	Bit 3 of Port 5, General Purpose Input
	ADC0_CH3	I	In/A	Analog Input Channel 3 for ADC0
	T3INA	I	In/A	GPT12E Timer T3 Count/Gate Input
28	P5.4	I	In/A	Bit 4 of Port 5, General Purpose Input
	ADC0_CH4	I	In/A	Analog Input Channel 4 for ADC0
	T3EUDA	I	In/A	GPT12E Timer T3 External Up/Down Control Input
	TMS_A	I	In/A	JTAG Test Mode Selection Input
29	P5.5	I	In/A	Bit 5 of Port 5, General Purpose Input
	ADC0_CH5	I	In/A	Analog Input Channel 5 for ADC0
	CCU60_T12 HRB	I	In/A	External Run Control Input for T12 of CCU60
30	P5.8	I	In/A	Bit 8 of Port 5, General Purpose Input
	ADC0_CH8	I	In/A	Analog Input Channel 8 for ADC0
	ADC1_CH8	I	In/A	Analog Input Channel 8 for ADC1
	CCU6x_T12H RC	I	In/A	External Run Control Input for T12 of CCU60/1
	CCU6x_T13H RC	I	In/A	External Run Control Input for T13 of CCU60/1
	U2C0_DX0F	I	In/A	USIC2 Channel 0 Shift Data Input

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
54	P2.7	O0 / I	St/B	Bit 7 of Port 2, General Purpose Input/Output
	U0C1_SELO0	O1	St/B	USIC0 Channel 1 Select/Control 0 Output
	U0C0_SELO1	O2	St/B	USIC0 Channel 0 Select/Control 1 Output
	CC2_CC20	O3 / I	St/B	CAPCOM2 CC20IO Capture Inp./ Compare Out.
	A20	OH	St/B	External Bus Interface Address Line 20
	U0C1_DX2C	I	St/B	USIC0 Channel 1 Shift Control Input
	RxDC1C	I	St/B	CAN Node 1 Receive Data Input
	ESR2_7	I	St/B	ESR2 Trigger Input 7
55	P0.1	O0 / I	St/B	Bit 1 of Port 0, General Purpose Input/Output
	U1C0_DOUT	O1	St/B	USIC1 Channel 0 Shift Data Output
	TxDC0	O2	St/B	CAN Node 0 Transmit Data Output
	CCU61_CC61	O3	St/B	CCU61 Channel 1 Output
	A1	OH	St/B	External Bus Interface Address Line 1
	U1C0_DX0B	I	St/B	USIC1 Channel 0 Shift Data Input
	CCU61_CC61INA	I	St/B	CCU61 Channel 1 Input
	U1C0_DX1A	I	St/B	USIC1 Channel 0 Shift Clock Input
56	P2.8	O0 / I	DP/B	Bit 8 of Port 2, General Purpose Input/Output
	U0C1_SCLKOUT	O1	DP/B	USIC0 Channel 1 Shift Clock Output
	EXTCLK	O2	DP/B	Programmable Clock Signal Output¹⁾
	CC2_CC21	O3 / I	DP/B	CAPCOM2 CC21IO Capture Inp./ Compare Out.
	A21	OH	DP/B	External Bus Interface Address Line 21
	U0C1_DX1D	I	DP/B	USIC0 Channel 1 Shift Clock Input

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
57	P2.9	O0 / I	St/B	Bit 9 of Port 2, General Purpose Input/Output
	U0C1_DOUT	O1	St/B	USIC0 Channel 1 Shift Data Output
	TxDC1	O2	St/B	CAN Node 1 Transmit Data Output
	CC2_CC22	O3 / I	St/B	CAPCOM2 CC22IO Capture Inp./ Compare Out.
	A22	OH	St/B	External Bus Interface Address Line 22
	CLKIN1	I	St/B	Clock Signal Input 1
	TCK_A	IH	St/B	DAP0/JTAG Clock Input If JTAG pos. A is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it. If DAP pos. 0 is selected during start-up, an internal pull-down device will hold this pin low when nothing is driving it.
58	P0.2	O0 / I	St/B	Bit 2 of Port 0, General Purpose Input/Output
	U1C0_SCLK OUT	O1	St/B	USIC1 Channel 0 Shift Clock Output
	TxDC0	O2	St/B	CAN Node 0 Transmit Data Output
	CCU61_CC6 2	O3	St/B	CCU61 Channel 2 Output
	A2	OH	St/B	External Bus Interface Address Line 2
	U1C0_DX1B	I	St/B	USIC1 Channel 0 Shift Clock Input
	CCU61_CC6 2INA	I	St/B	CCU61 Channel 2 Input

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
81	P1.1	O0 / I	St/B	Bit 1 of Port 1, General Purpose Input/Output
	U1C0_SELO5	O2	St/B	USIC1 Channel 0 Select/Control 5 Output
	U2C1_DOUT	O3	St/B	USIC2 Channel 1 Shift Data Output
	A9	OH	St/B	External Bus Interface Address Line 9
	ESR2_3	I	St/B	ESR2 Trigger Input 3
	U2C1_DX0C	I	St/B	USIC2 Channel 1 Shift Data Input
82	P10.10	O0 / I	St/B	Bit 10 of Port 10, General Purpose Input/Output
	U0C0_SELO0	O1	St/B	USIC0 Channel 0 Select/Control 0 Output
	CCU60_COUT63	O2	St/B	CCU60 Channel 3 Output
	AD10	OH / IH	St/B	External Bus Interface Address/Data Line 10
	U0C0_DX2C	I	St/B	USIC0 Channel 0 Shift Control Input
	U0C1_DX1A	I	St/B	USIC0 Channel 1 Shift Clock Input
	TDI_B	IH	St/B	JTAG Test Data Input If JTAG pos. B is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it.
83	P10.11	O0 / I	St/B	Bit 11 of Port 10, General Purpose Input/Output
	U1C0_SCLKOUT	O1	St/B	USIC1 Channel 0 Shift Clock Output
	BRKOUT	O2	St/B	OCDS Break Signal Output
	AD11	OH / IH	St/B	External Bus Interface Address/Data Line 11
	U1C0_DX1D	I	St/B	USIC1 Channel 0 Shift Clock Input
	TMS_B	IH	St/B	JTAG Test Mode Selection Input If JTAG pos. B is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it.

3 Functional Description

The architecture of the XE164xN combines advantages of RISC, CISC, and DSP processors with an advanced peripheral subsystem in a well-balanced design. On-chip memory blocks allow the design of compact systems-on-silicon with maximum performance suited for computing, control, and communication.

The on-chip memory blocks (program code memory and SRAM, dual-port RAM, data SRAM) and the generic peripherals are connected to the CPU by separate high-speed buses. Another bus, the LXBus, connects additional on-chip resources and external resources. This bus structure enhances overall system performance by enabling the concurrent operation of several subsystems of the XE164xN.

The block diagram gives an overview of the on-chip components and the advanced internal bus structure of the XE164xN.

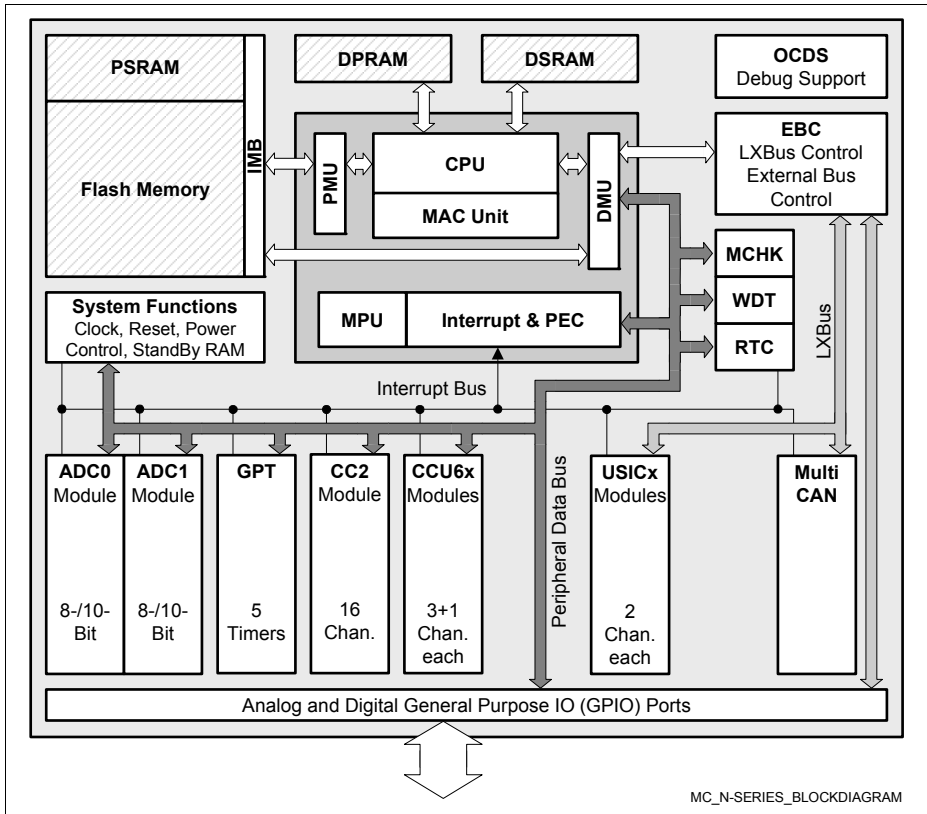


Figure 4 Block Diagram

3.3 Central Processing Unit (CPU)

The core of the CPU consists of a 5-stage execution pipeline with a 2-stage instruction-fetch pipeline, a 16-bit arithmetic and logic unit (ALU), a 32-bit/40-bit multiply and accumulate unit (MAC), a register-file providing three register banks, and dedicated SFRs. The ALU features a multiply-and-divide unit, a bit-mask generator, and a barrel shifter.

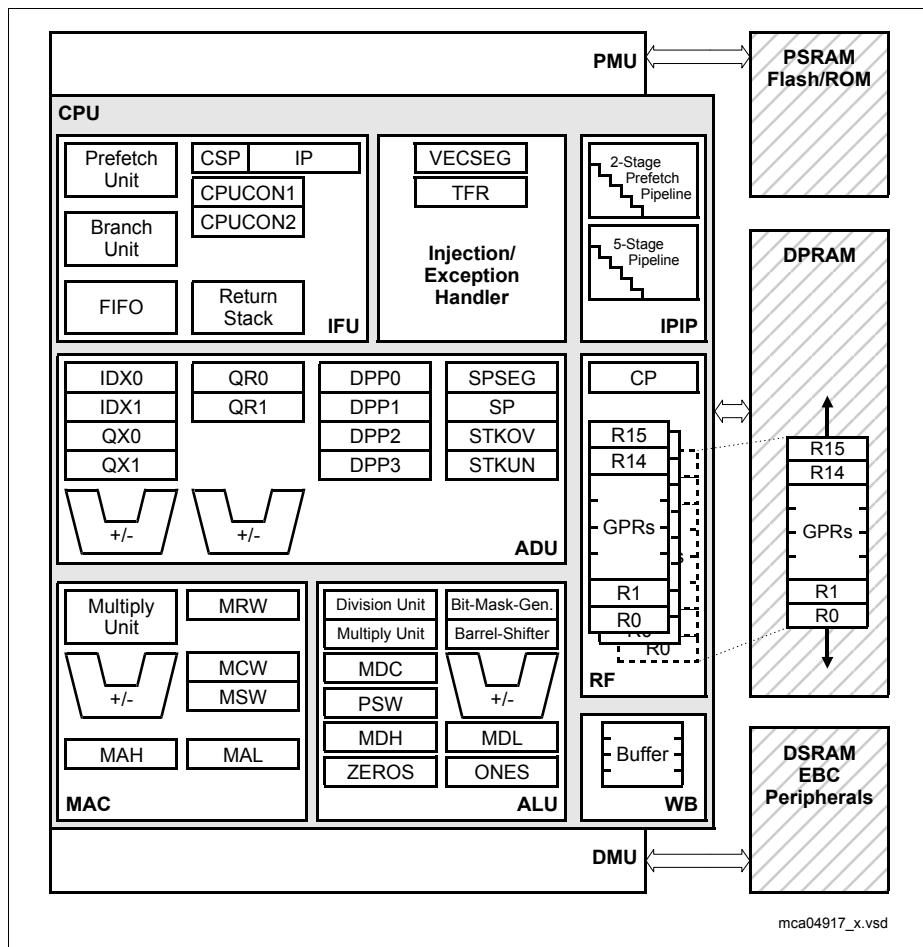


Figure 5 CPU Block Diagram

3.19 Instruction Set Summary

Table 10 lists the instructions of the XE164xN.

The addressing modes that can be used with a specific instruction, the function of the instructions, parameters for conditional execution of instructions, and the opcodes for each instruction can be found in the **“Instruction Set Manual”**.

This document also provides a detailed description of each instruction.

Table 10 Instruction Set Summary

Mnemonic	Description	Bytes
ADD(B)	Add word (byte) operands	2 / 4
ADDC(B)	Add word (byte) operands with Carry	2 / 4
SUB(B)	Subtract word (byte) operands	2 / 4
SUBC(B)	Subtract word (byte) operands with Carry	2 / 4
MUL(U)	(Un)Signed multiply direct GPR by direct GPR (16- × 16-bit)	2
DIV(U)	(Un)Signed divide register MDL by direct GPR (16-/16-bit)	2
DIVL(U)	(Un)Signed long divide reg. MD by direct GPR (32-/16-bit)	2
CPL(B)	Complement direct word (byte) GPR	2
NEG(B)	Negate direct word (byte) GPR	2
AND(B)	Bitwise AND, (word/byte operands)	2 / 4
OR(B)	Bitwise OR, (word/byte operands)	2 / 4
XOR(B)	Bitwise exclusive OR, (word/byte operands)	2 / 4
BCLR/BSET	Clear/Set direct bit	2
BMOV(N)	Move (negated) direct bit to direct bit	4
BAND/BOR/BXOR	AND/OR/XOR direct bit with direct bit	4
BCMP	Compare direct bit to direct bit	4
BFLDH/BFLDL	Bitwise modify masked high/low byte of bit-addressable direct word memory with immediate data	4
CMP(B)	Compare word (byte) operands	2 / 4
CMPD1/2	Compare word data to GPR and decrement GPR by 1/2	2 / 4
CMPI1/2	Compare word data to GPR and increment GPR by 1/2	2 / 4
PRIOR	Determine number of shift cycles to normalize direct word GPR and store result in direct word GPR	2
SHL/SHR	Shift left/right direct word GPR	2

Electrical Parameters

4.3.1 DC Parameters for Upper Voltage Area

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV} .

Note: Operating Conditions apply.

Table 15 is valid under the following conditions: $V_{DDP} \leq 5.5 \text{ V}$; $V_{DDP} \text{ typ. } 5 \text{ V}$; $V_{DDP} \geq 4.5 \text{ V}$

Table 15 DC Characteristics for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Pin capacitance (digital inputs/outputs). To be doubled for double bond pins. ¹⁾	$C_{IO} \text{ CC}$	–	–	10	pF	not subject to production test
Input Hysteresis ²⁾	$HYS \text{ CC}$	$0.11 \times V_{DDP}$	–	–	V	$R_S = 0 \text{ Ohm}$
Absolute input leakage current on pins of analog ports ³⁾	$ I_{OZ1} \text{ CC}$	–	10	200	nA	$V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
Absolute input leakage current for all other pins. To be doubled for double bond pins. ³⁾¹⁾⁴⁾	$ I_{OZ2} \text{ CC}$	–	0.2	5	μA	$T_J \leq 110 \text{ }^\circ\text{C}$; $V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
		–	0.2	15	μA	$T_J \leq 150 \text{ }^\circ\text{C}$; $V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
Pull Level Force Current ⁵⁾	$ I_{PLF} \text{ SR}$	250	–	–	μA	$V_{IN} \geq V_{IHmin}(\text{pull down_enabled})$; $V_{IN} \leq \bar{V}_{ILmax}(\text{pull up_enabled})$
Pull Level Keep Current ⁶⁾	$ I_{PLK} \text{ SR}$	–	–	30	μA	$V_{IN} \geq V_{IHmin}(\text{pull up_enabled})$; $V_{IN} \leq V_{ILmax}(\text{pull down_enabled})$
Input high voltage (all except XTAL1)	$V_{IH} \text{ SR}$	$0.7 \times V_{DDP}$	–	$V_{DDP} + 0.3$	V	
Input low voltage (all except XTAL1)	$V_{IL} \text{ SR}$	-0.3	–	$0.3 \times V_{DDP}$	V	

Electrical Parameters

- 2) This parameter is tested for the fastest and the slowest selection. The medium selections are not subject to production test - verified by design/characterization
- 3) f_{WU} in MHz
- 4) This value includes a hysteresis of approximately 50 mV for rising voltage.
- 5) V_{LV} = selected SWD voltage level
- 6) The limit $V_{LV} - 0.10$ V is valid for the OK1 level. The limit for the OK2 level is $V_{LV} - 0.15$ V.

Conditions for t_{SPO} Timing Measurement

The time required for the transition from **Power-on** to **Base** mode is called t_{SPO} . It is measured under the following conditions:

Precondition: The pad supply is valid, i.e. V_{DDPB} is above 3.0V and remains above 3.0V even though the XE164xN is starting up. No debugger is attached.

Start condition: Power-on reset is removed ($\overline{PORST} = 1$).

End condition: External pin toggle caused by first user instruction executed from FLASH after startup.

Conditions for t_{SSO} Timing Measurement

The time required for the transition from **Stopover** to **Stopover Waked-Up** mode is called t_{SSO} . It is measured under the following conditions:

Precondition: The **Stopover** mode has been entered using the procedure defined in the Programmer's Guide.

Start condition: Pin toggle on $\overline{ESR}$ pin triggering the startup sequence.

End condition: External pin toggle caused by first user instruction executed from PSRAM after startup.

Coding of bit fields LEVxV in SWD Configuration Registers

After power-on the supply watch dog is preconfigured to operate in the lower voltage range.

Table 22 Coding of bit fields LEVxV in Register SWDCON0

Code	Voltage Level	Notes ¹⁾
0000 _B	-	out of valid operation range
0001 _B	3.0 V	LEV1V: reset request
0010 _B - 0101 _B	3.1 V - 3.4 V	step width is 0.1 V
0110 _B	3.6 V	
0111 _B	4.0 V	
1000 _B	4.2 V	
1001 _B	4.5 V	LEV2V: no request
1010 _B - 1110 _B	4.6 V - 5.0 V	step width is 0.1 V
1111 _B	5.5 V	

1) The indicated default levels for LEV1V and LEV2V are selected automatically after a power-on reset.

Coding of bit fields LEVxV in PVC Configuration Registers

The core voltages are controlled internally to the nominal value of 1.5 V; a variation of $\pm 10\%$ is allowed. These operation conditions limit the possible PVC monitoring values to the predefined reset values shown in [Table 23](#).

Table 23 Coding of bit fields LEVxV in Registers PVCyCONz

Code	Voltage Level	Notes ¹⁾
000 _B -011 _B	-	out of valid operation range
100 _B	1.35 V	LEV1V: reset request
101 _B	1.45 V	LEV2V: interrupt request ²⁾
110 _B - 111 _B	-	out of valid operation range

1) The indicated default levels for LEV1V and LEV2V are selected automatically after a power-on reset.

2) Due to variations of the tolerance of both the Embedded Voltage Regulators (EVR) and the PVC levels, this interrupt can be triggered inadvertently, even though the core voltage is within the normal range. It is, therefore, recommended not to use this warning level.

4.6 Flash Memory Parameters

The XE164xN is delivered with all Flash sectors erased and with no protection installed. The data retention time of the XE164xN's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 24 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	2 ¹⁾		$N_{FL_RD} \leq 1$
		–	–	1 ²⁾		$N_{FL_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycles	$t_{RET} \geq 20$ years
Flash wait states ³⁾	N_{WSFLAS} H SR	1	–	–		$f_{SYS} \leq 8$ MHz
		2	–	–		$f_{SYS} \leq 13$ MHz
		3	–	–		$f_{SYS} \leq 17$ MHz
		4	–	–		$f_{SYS} > 17$ MHz
Erase time per sector/page	t_{ER} CC	–	7 ⁴⁾	8.0	ms	
Programming time per page	t_{PR} CC	–	3 ⁴⁾	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	years	$N_{ER} \leq 1,000$ cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycles	
Number of erase cycles	N_{ER} SR	–	–	15.000	cycles	$t_{RET} \geq 5$ years; Valid for Flash module 1 (up to 64 kbytes)
		–	–	1.000	cycles	$t_{RET} \geq 20$ years

1) The unused Flash module(s) can be erased/programmed while code is executed and/or data is read from only one Flash module or from PSRAM. The Flash module that delivers code/data can, of course, not be erased/programmed.

4.7 AC Parameters

These parameters describe the dynamic behavior of the XE164xN.

4.7.1 Testing Waveforms

These values are used for characterization and production testing (except pin XTAL1).

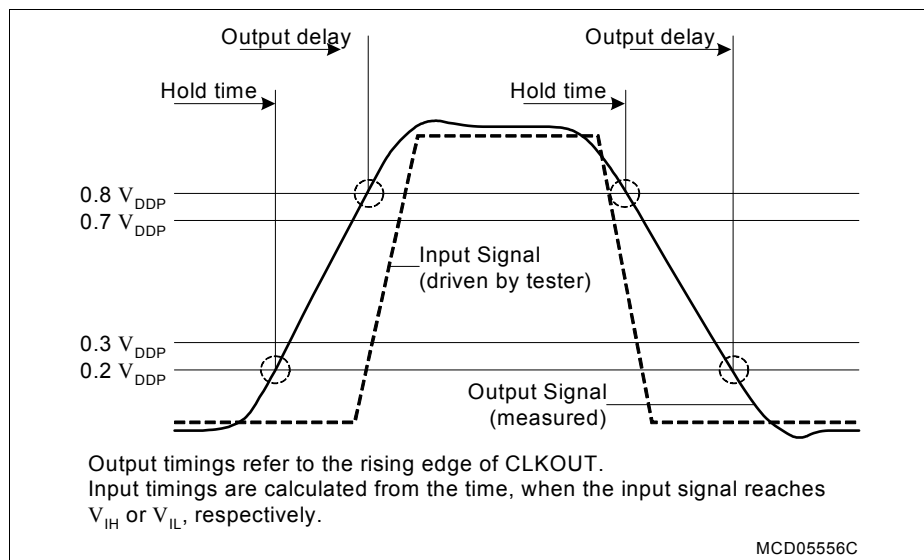


Figure 17 Input Output Waveforms

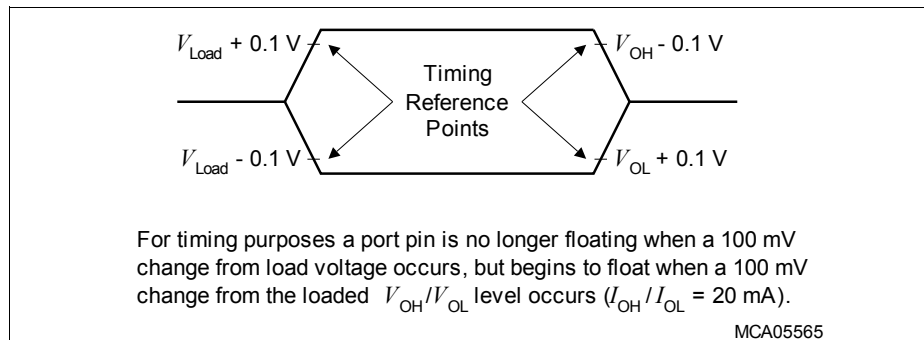


Figure 18 Floating Waveforms

Electrical Parameters

Table 28 Standard Pad Parameters for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Rise and Fall times (10% - 90%)	t_{RF} CC	—	—	37 + 0.65 x C_L	ns	$C_L \geq 20$ pF; $C_L \leq 100$ pF; Driver_Strength = Medium
		—	—	24 + 0.3 x C_L	ns	$C_L \geq 20$ pF; $C_L \leq 100$ pF; Driver_Strength = Strong ; Driver_Edge= Medium
		—	—	6.2 + 0.24 x C_L	ns	$C_L \geq 20$ pF; $C_L \leq 100$ pF; Driver_Strength = Strong ; Driver_Edge= Sharp
		—	—	34 + 0.3 x C_L	ns	$C_L \geq 20$ pF; $C_L \leq 100$ pF; Driver_Strength = Strong ; Driver_Edge= Slow
		—	—	500 + 2.5 x C_L	ns	$C_L \geq 20$ pF; $C_L \leq 100$ pF; Driver_Strength = Weak

1) An output current above $|I_{Oxnom}|$ may be drawn from up to three pins at the same time. For any group of 16 neighboring output pins, the total output current in each direction (ΣI_{OL} and $\Sigma -I_{OH}$) must remain below 50 mA.

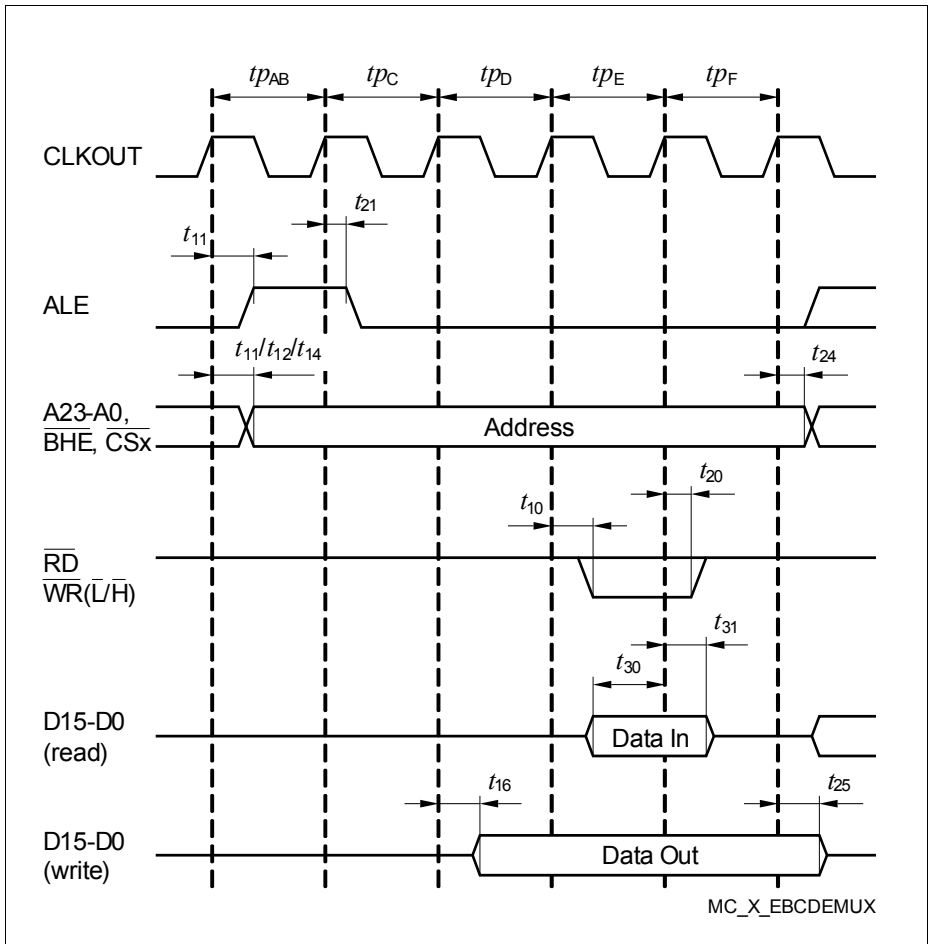


Figure 24 Demultiplexed Bus Cycle

4.7.5.1 Bus Cycle Control with the READY Input

The duration of an external bus cycle can be controlled by the external circuit using the READY input signal. The polarity of this input signal can be selected.

Synchronous READY permits the shortest possible bus cycle but requires the input signal to be synchronous to the reference signal CLKOUT.

An asynchronous READY signal puts no timing constraints on the input signal but incurs a minimum of one waitstate due to the additional synchronization stage. The minimum

Table 34 USIC SSC Master Mode Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Slave select output SELO active to first SCLKOUT transmit edge	t_1 CC	$t_{\text{SYS}} - 10^{1)}$	—	—	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t_2 CC	$t_{\text{SYS}} - 9^{1)}$	—	—	ns	
Data output DOUT valid time	t_3 CC	-7	—	11	ns	
Receive data input setup time to SCLKOUT receive edge	t_4 SR	40	—	—	ns	
Data input DX0 hold time from SCLKOUT receive edge	t_5 SR	-5	—	—	ns	

1) $t_{\text{SYS}} = 1 / f_{\text{SYS}}$

Table 35 is valid under the following conditions: $C_L = 20$ pF; SSC= slave ; voltage_range= upper

Table 35 USIC SSC Slave Mode Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Select input DX2 setup to first clock input DX1 transmit edge ¹⁾	t_{10} SR	7	—	—	ns	
Select input DX2 hold after last clock input DX1 receive edge ¹⁾	t_{11} SR	7	—	—	ns	
Receive data input setup time to shift clock receive edge ¹⁾	t_{12} SR	7	—	—	ns	

Table 38 DAP Interface Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
DAP0 clock period ¹⁾	t_{11} SR	25	—	—	ns	
DAP0 high time	t_{12} SR	8	—	—	ns	
DAP0 low time ¹⁾	t_{13} SR	8	—	—	ns	
DAP0 clock rise time	t_{14} SR	—	—	4	ns	
DAP0 clock fall time	t_{15} SR	—	—	4	ns	
DAP1 setup to DAP0 rising edge	t_{16} SR	6	—	—	ns	
DAP1 hold after DAP0 rising edge	t_{17} SR	6	—	—	ns	
DAP1 valid per DAP0 clock period ²⁾	t_{19} CC	12	17	—	ns	

1) See the DAP chapter for clock rate restrictions in the Active::IDLE protocol state.

2) The Host has to find a suitable sampling point by analyzing the sync telegram response.

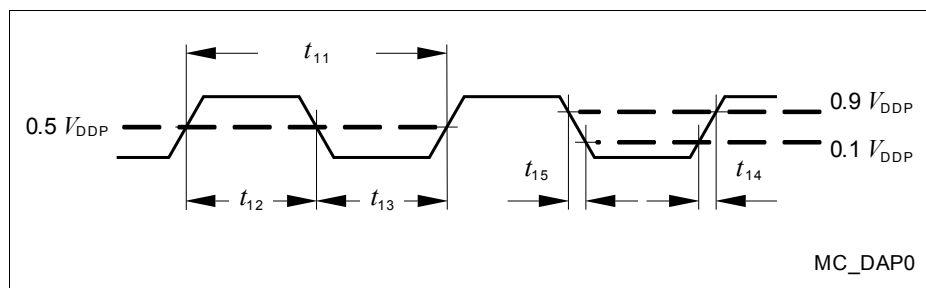


Figure 27 Test Clock Timing (DAP0)

Electrical Parameters

Table 39 JTAG Interface Timing for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK low time	t_3 SR	16	—	—	ns	
TCK clock rise time	t_4 SR	—	—	8	ns	
TCK clock fall time	t_5 SR	—	—	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	—	—	ns	
TDI/TMS hold after TCK rising edge	t_7 SR	6	—	—	ns	
TDO valid from TCK falling edge (propagation delay) ²⁾	t_8 CC	—	25	29	ns	
TDO high impedance to valid output from TCK falling edge ³⁾²⁾	t_9 CC	—	25	29	ns	
TDO valid output to high impedance from TCK falling edge ²⁾	t_{10} CC	—	25	29	ns	
TDO hold after TCK falling edge ²⁾	t_{18} CC	5	—	—	ns	

1) Under typical conditions, the JTAG interface can operate at transfer rates up to 20 MHz.

2) The falling edge on TCK is used to generate the TDO timing.

3) The setup time for TDO is given implicitly by the TCK cycle time.

Table 40 is valid under the following conditions: $C_L = 20$ pF; voltage_range= lower

Table 40 JTAG Interface Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	t_1 SR	50	—	—	ns	
TCK high time	t_2 SR	16	—	—	ns	
TCK low time	t_3 SR	16	—	—	ns	
TCK clock rise time	t_4 SR	—	—	8	ns	
TCK clock fall time	t_5 SR	—	—	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	—	—	ns	

Electrical Parameters

Table 40 JTAG Interface Timing for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TDI/TMS hold after TCK rising edge	t_7 SR	6	—	—	ns	
TDO valid from TCK falling edge (propagation delay) ¹⁾	t_8 CC	—	32	36	ns	
TDO high impedance to valid output from TCK falling edge ²⁾¹⁾	t_9 CC	—	32	36	ns	
TDO valid output to high impedance from TCK falling edge ¹⁾	t_{10} CC	—	32	36	ns	
TDO hold after TCK falling edge ¹⁾	t_{18} CC	5	—	—	ns	

1) The falling edge on TCK is used to generate the TDO timing.

2) The setup time for TDO is given implicitly by the TCK cycle time.

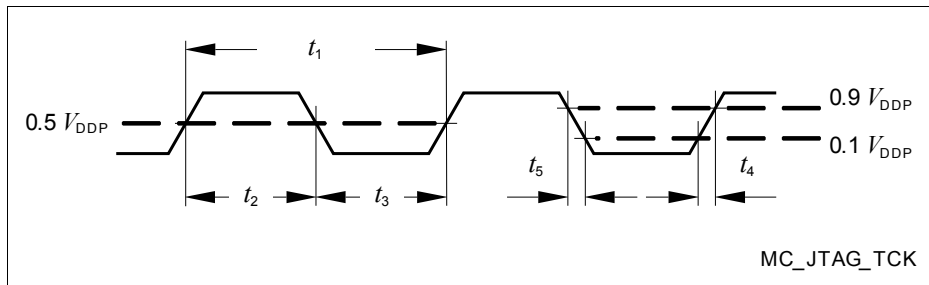


Figure 30 Test Clock Timing (TCK)